

## NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE0157A2 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

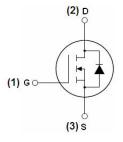
- $V_{DS} = 100V, I_D = 57A$  $R_{DS(ON)} < 12.5mΩ @ V_{GS} = 10V$  (Typ:14.5mΩ)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

#### **Application**

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-220-3L top view

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0157A2	NCE0157A2	TO-220-3L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	100	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	57	А
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100℃)	40	Α
Pulsed Drain Current	I <sub>DM</sub>	160	Α
Maximum Power Dissipation	P <sub>D</sub>	160	W
Derating factor	-	1.06	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	580	mJ



# NCE0157A2

Operating Junction and Storage Temperature Range T <sub>J</sub> ,T <sub>STG</sub>	-55 To 175 °C
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## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	Rejc	0.94	°C/W	ĺ
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## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	100	110	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =28A	-	12.5	14.5	mΩ
Forward Transconductance	<b>G</b> FS	V <sub>DS</sub> =25V,I <sub>D</sub> =28A	32	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss	\/ OF\/\/ O\/	-	3969	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,	-	182.5	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	160.2	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	17	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =30V, $I_{D}$ =2A, $R_{L}$ =15 $\Omega$	-	13	-	nS
Turn-Off Delay Time	$t_{\sf d(off)}$	$V_{GS}$ =10V, $R_{G}$ =2.5 $\Omega$	-	55	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	16	-	nS
Total Gate Charge	Qg	)/ 20)/I 20A	-	146.1	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V,I <sub>D</sub> =30A, V <sub>GS</sub> =10V	-	29.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	VGS-10V	-	57.1	-	nC
Drain-Source Diode Characteristics	V					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =28A	-	0.85	1.2	V
Diode Forward Current (Note 2)	Is		-	-	57	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 28A	-	35	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>		58	-	nC
Forward Turn-On Time	On Time t <sub>on</sub> Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				y LS+LD)	

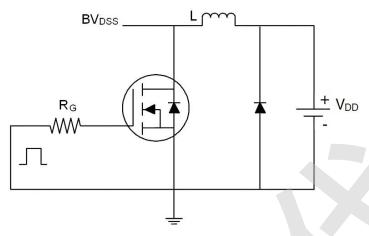
## Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25  $^{\circ}\text{C}$  ,VDD=50V,VG=10V,Rg=25 $\Omega$  , L=1mH, IAS=35A

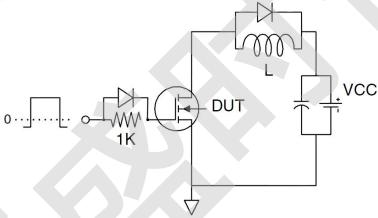


## **Test Circuit**

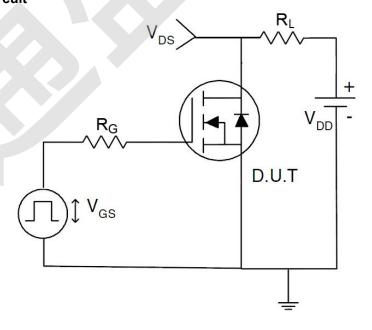
## 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

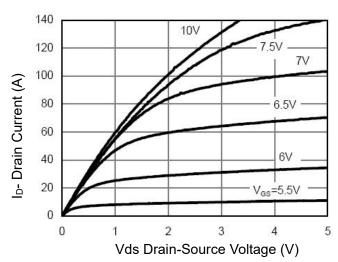


## 3) Switch Time Test Circuit

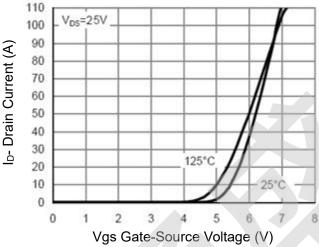




## **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

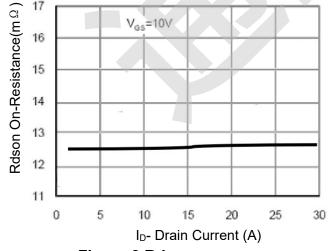


Figure 3 Rdson- Drain Current

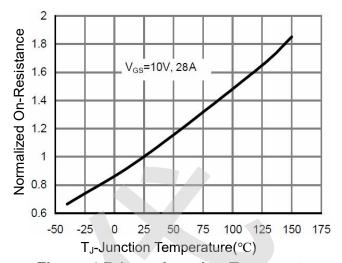


Figure 4 Rdson-Junction Temperature

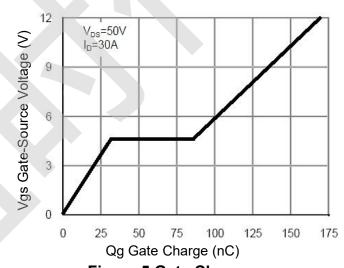


Figure 5 Gate Charge

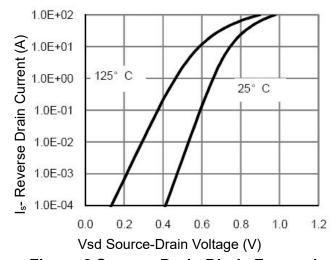
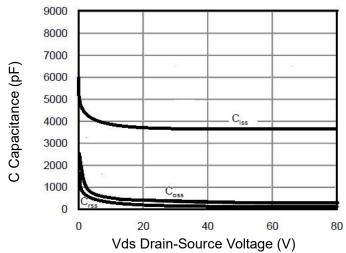
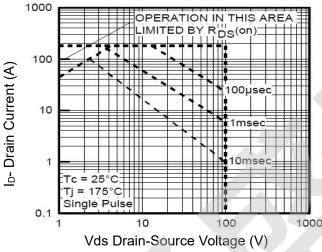


Figure 6 Source- Drain Diode Forward









**Figure 8 Safe Operation Area** 

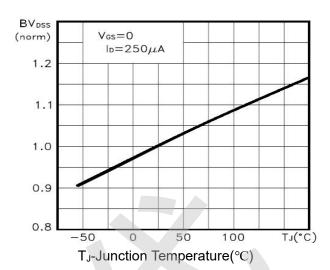


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

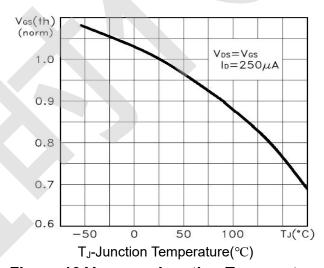
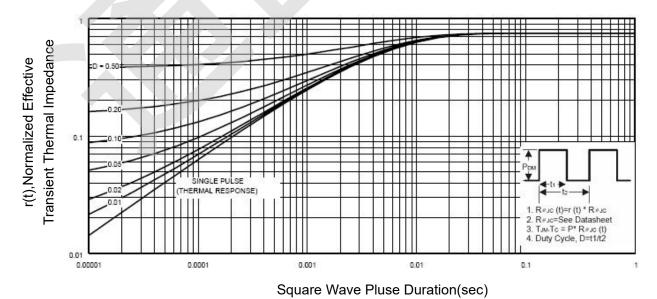


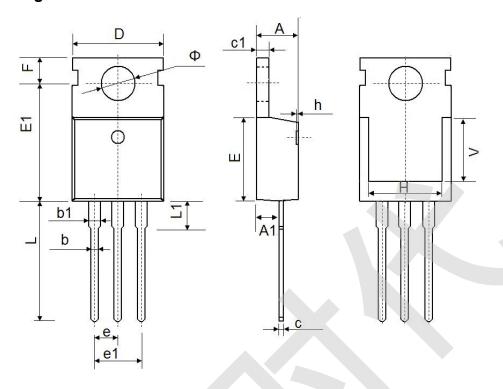
Figure 10 V<sub>GS(th)</sub> vs Junction Temperature



**Figure 11 Normalized Maximum Transient Thermal Impedance** 



# **TO-220-3L Package Information**



Comple of	Dimensions	In Millimeters	Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
A	4.400	4.600	0.173	0.181		
A1	2.250	2.550	0.089	0.100		
b	0.710	0.910	0.028	0.036		
b1	1.170	1.370	0.046	0.054		
С	0.330	0.650	0.013	0.026		
c1	1.200	1.400	0.047	0.055		
D	9.910	10.250	0.390	0.404		
E	8.9500	9.750	0.352	0.384		
E1	12.650	12.950	0.498	0.510		
е	2.540	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204		
F	2.650	2.950	0.104	0.116		
Н	7.900	8.100	0.311	0.319		
h	0.000	0.300	0.000	0.012		
L	12.900	13.400	0.508	0.528		
L1	2.850	3.250	0.112	0.128		
V	7.500	REF.	0.295 REF.			
Ф	3.400	3.800	0.134	0.150		





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